

BAT54T

Single Schottky barrier diode

Rev. 01 — 14 December 2009

Product data sheet

1. Product profile

1.1 General description

Single planar Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOT416 (SC-75) ultra small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low forward voltage: max. 400 mV
- Low capacitance: max. 10 pF
- Ultra small SMD plastic package
- AEC-Q101 qualified

1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diode

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		-	-	200	mA
V_R	reverse voltage		-	-	30	V
V _F	forward voltage	$I_F = 10 \text{ mA}$	<u>[1]</u> _	-	400	mV

[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	anode		
2	not connected	3	3
3	cathode	1 2	1 2 n.c. 006aaa436

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BAT54T	SC-75	plastic surface-mounted package; 3 leads	SOT416			

4. Marking

Table 4. Marking codes

Type number	Marking code
BAT54T	ZW

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	30	V
I _F	forward current		-	200	mA
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ s; } \delta \leq 0.5$	-	300	mA
I _{FSM}	non-repetitive peak	square wave			
	forward current	$t_p = 100 \ \mu s$	-	4	А
		$t_p = 1 \text{ ms}$	-	2	А
		$t_p = 10 \text{ ms}$	-	1	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	150	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	833	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[2] -	-	350	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

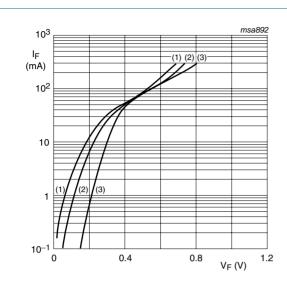
unio		•				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		$I_F = 0.1 \text{ mA}$	-	-	240	mV
		I _F = 1 mA	-	-	320	mV
		I _F = 10 mA	-	-	400	mV
		$I_F = 30 \text{ mA}$	-	-	500	mV
		I _F = 100 mA	-	-	800	mV
I _R	reverse current	V _R = 25 V	-	-	2	μΑ
t _{rr}	reverse recovery time		[2] -	-	5	ns
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	-	10	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

^[2] Soldering point of cathode tab.

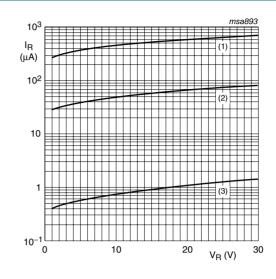
^[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

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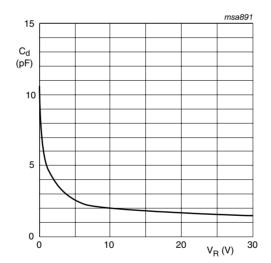
- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

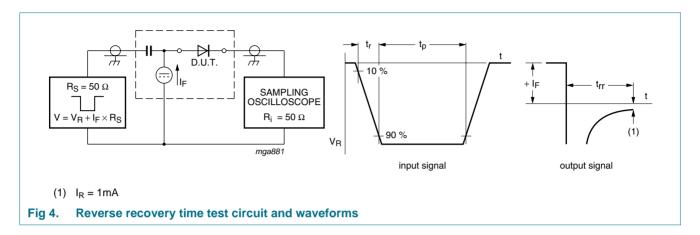


 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

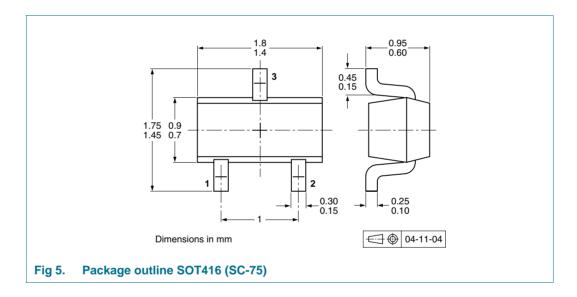
Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Test information



9. Package outline



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10. Packing information

Table 8. **Packing methods**

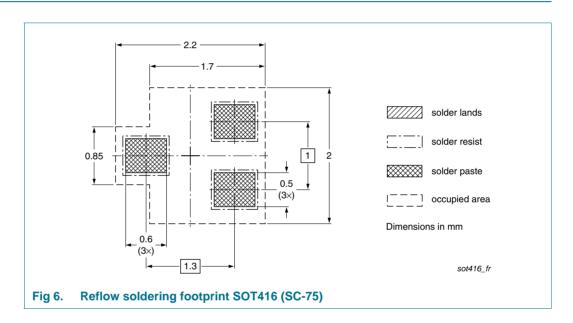
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BAT54T	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering

Product data sheet



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12. Revision history

Table 9. **Revision history**

Product data sheet

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAT54T_1	20091214	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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